

N-channel 25 V 1.15 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 1 — 2 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

1.4 Quick reference data

Table 1. Quick reference data

- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance
- Power OR-ing
- Server power supplies
- Sync rectifier

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	25	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u> _	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	215	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ T _j = 25 °C; see <u>Figure 12</u>	-	1.2	1.5	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u>	-	0.95	1.15	mΩ



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Table 1.	Quick reference data	continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \ \text{V;} \ \text{I}_{D} = 25 \ \text{A;} \\ V_{DS} = 12 \ \text{V;} \ \text{see} \ \underline{\text{Figure 14}}; \\ \text{see} \ \underline{\text{Figure 15}} \end{array}$	-	11	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 12 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	39	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		5
2	S	source	mb	
3	S	source		
4	G	gate	q ;	
mb	D	mounting base; connected to drain	$\begin{array}{c} \hline 1 & 2 & 3 & 4 \end{array}$	mbb076 S
			SOT669 (LFPAK; Power-SO8)	

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN1R1-25YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669			

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
PSMN1R1-25YLC	1C125L

[1] % = placeholder for manufacturing site code.

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5. Limiting values

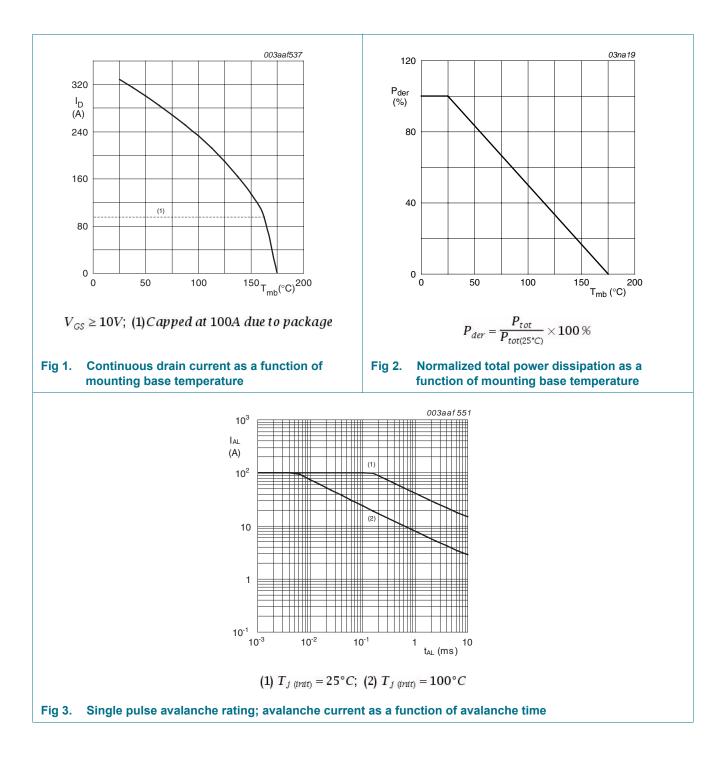
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	25	V
V _{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	25	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u> [1]	-	100	А
		V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u> [1]	-	100	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 4</u>	-	1318	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	215	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	810	-	V
Source-drain	n diode				
I _S	source current	T _{mb} = 25 °C	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; T_{mb} = 25 °C	-	1318	А
Avalanche ru	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 ^{\circ}\text{C}; \text{I}_{\text{D}} = 100 \text{ A}; \\ V_{sup} \leq 25 \text{ V}; \text{ unclamped}; \text{R}_{\text{GS}} = 50 \Omega; \\ see \underline{\text{Figure 3}} $	-	253	mJ

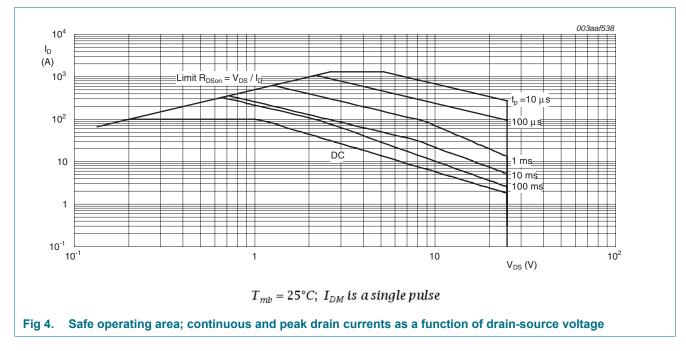
[1] Continuous current is limited by package.

PSMN1R1-25YLC



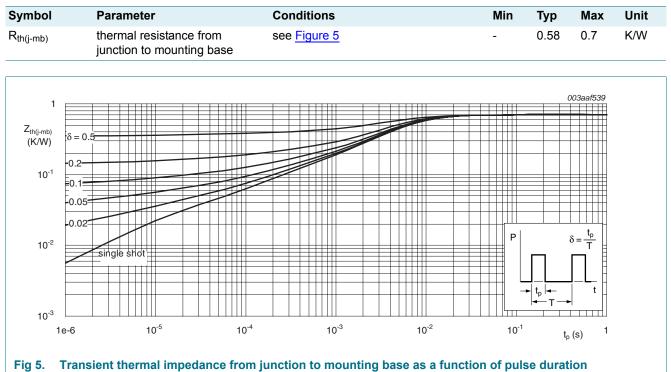
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6. Thermal characteristics

Table 6.Thermal characteristics



N-channel 25 V 1.15 m Ω logic level MOSFET in LFPAK using

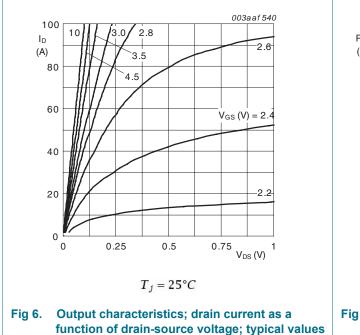
7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C	25	-	-	V
()	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _i = -55 °C	22.5	-	-	V
	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 10; see Figure 11	1.05	1.43	1.95	V
		I _D = 10 mA; V _{DS} = V _{GS} ; T _i = 150 °C	0.5	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _i = -55 °C	-	-	2.25	V
I _{DSS}	drain leakage current	V _{DS} = 25 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 25 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u>	-	1.2	1.5	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 150 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	2.45	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u>	-	0.95	1.15	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	1.8	mΩ
R _G	gate resistance	f = 1 MHz	-	1.1	2.2	Ω
Dynamic cł	naracteristics					
Q _{G(tot)} total gate ch	total gate charge	I_D = 25 A; V_{DS} = 12 V; V_{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	83	-	nC
		I_D = 25 A; V_{DS} = 12 V; V_{GS} = 4.5 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	39	-	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V	-	75	-	nC
Q _{GS}	gate-source charge	I_D = 25 A; V_{DS} = 12 V; V_{GS} = 4.5 V;	-	11	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	8.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.9	-	nC
Q _{GD}	gate-drain charge		-	11	-	nC
V _{GS(pl)}	gate-source plateau voltage	I_D = 25 A; V_{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.3	-	V
C _{iss}	input capacitance	V_{DS} = 12 V; V_{GS} = 0 V; f = 1 MHz;	-	5287	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	1121	-	pF
C _{rss}	reverse transfer capacitance		-	406	-	pF
d(on)	turn-on delay time	V_{DS} = 12 V; R_L = 0.5 Ω ; V_{GS} = 4.5 V;	-	35	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	48	-	ns
d(off)	turn-off delay time		-	74	-	ns
	fall time		-	36	_	ns
t _f						

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Table 7.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 12 V; f = 1 MHz; T _j = 25 °C	-	22.6	-	nC
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.1	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	43	-	ns
Q _r	recovered charge	V _{DS} = 12 V	-	42	-	nC
t _a	reverse recovery rise time	V _{GS} = 0 V; I _S = 25 A; dI _S /dt = -100 A/µs; V _{DS} = 12 V; see <u>Figure 18</u>	-	25	-	ns
t _b	reverse recovery fall time		-	18	-	ns

Table 7. Characteristics ...continued



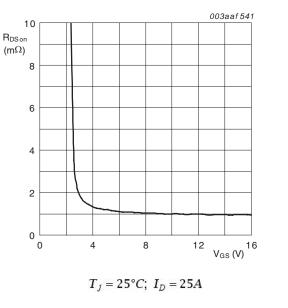
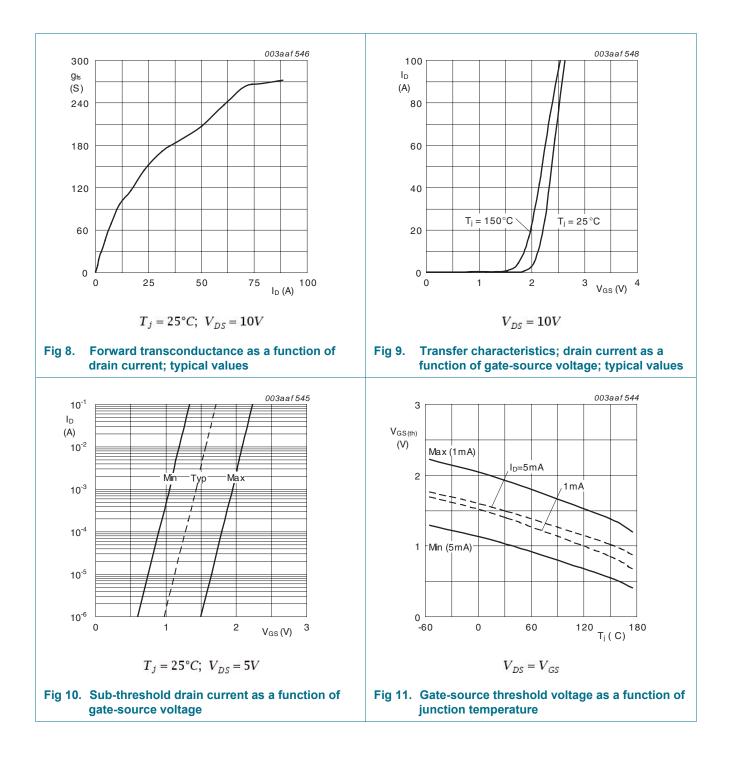
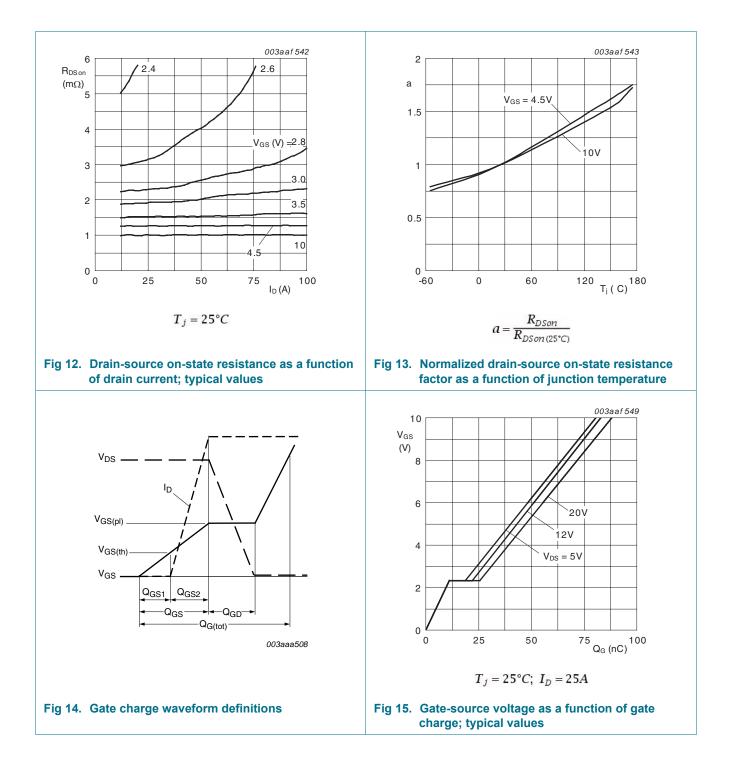


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

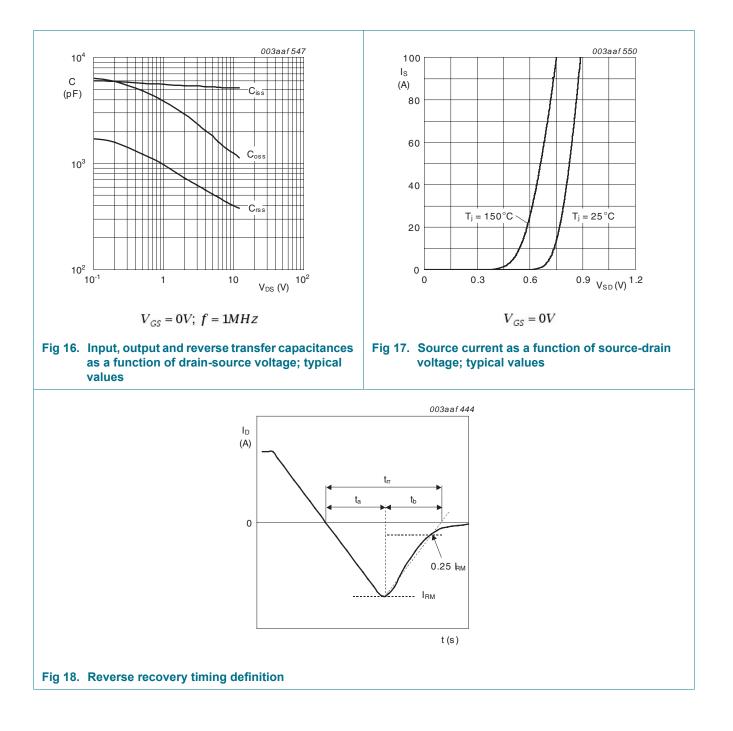
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PSMN1R1-25YLC



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8. Package outline

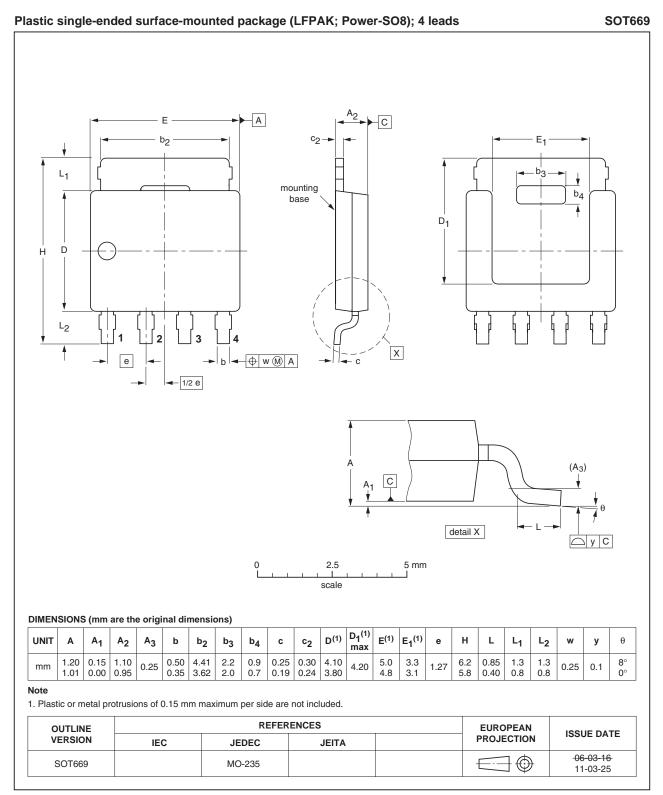


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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9. Revision history

Table 8. Revision h	8. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PSMN1R1-25YLC v.1	20110502	Product data sheet	-	-	

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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